PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble

Attorney Docket No.: 500462.04

Filed

: Concurrently herewith

Title

: BASE CURRENT REVERSAL SRAM MEMORY CELL AND METHOD

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicant wishes to make known to the Patent and Trademark Office the references set forth on the attached form PTO-1449. This application relies, under 35 U.S.C. § 120, on the earlier filing date of prior Application No. 10/284,984, filed October 30, 2002, which is continuation of United States Patent Application No. 09/757,683, filed January 8, 2001, issued December 3, 2002 as Patent No. 6,489,192 B2, which is a divisional of United States Patent Application No. 09/268,823, filed March 16, 1999, issued November 6, 2001 as Patent No. 6,313,490 B1. The references listed on the attached Form PTO-1449 were submitted to and/or cited by the Patent and Trademark Office in these prior applications and, therefore, are not required to be provided in this application. If the Examiner wishes, copies will be provided upon request. Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicant's duty to disclose all information he is aware of which is believed relevant to the examination of the above-identified application, applicant believes that his invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,

DORSEY & WHITNEY LLP

Kimton N. Eng Registration No. 43,605

KNE:asw

Enclosure:

Form PTO-1449

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500462.04 ids.doc 4846-1271-2704\1 FORM PTO-1449 (REV.7-80) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. APPLICATION NO. S00462.04 Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Wendell P. Noble

FILING DATE

GROUP ART UNIT

(Use several sheets if necessary)					FILING DATE Concurrently herewi	GROUP ART UNIT Not Yet Assi		gned		
			U.S.	PATENT 1	DOCUMENTS	-				
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS		SUBCLASS	FILING IF APPRO	DATE OPRIATI
	AA	4,810,667	03/07/89	Zorinsky	et al.	437		62		
	AB	4,881,105	11/14/89	Davari et al.		357		23.4		
	AC	5,194,396	03/16/93	Kim et al.		437		31		
····	AD	5,574,299	11/12/96	Kim		257		296		
	AE	5,592,005	01/07/97	Floyd et a	1.	257		331		
	AF	5,594,683	01/14/97	Chen et al	l	365		177		
	AG	6,075,272	06/13/00	Forbes et	al.	257		378		
	АН	6,229,161 B1	05/08/01	Nemati et	al.	257		133		
	AI	6,489,192 B2	12/03/02	Noble		438		202		
			FOREI	GN PATEN	NT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY		CLA	SS	SUBCLASS	TRANS	LATION
	AJ	JP359232437A	12/27/84	Japan					X	
	AK	10135235	05/22/98	Japan					X	
		ОТНЕ	R PRIOR A	RT (Including	Author, Title, Date, Pertinent Pa	iges, Etc.))			
	AL	l • • • • • • • • • • • • • • • • • • •	•		le Memory Cell", IBM rp. 1978, 3492-3494.	I Tech	nical l	Disclosur	e Bull	etin,
	AM	Jack Y.C. Sun, "CMOS Technology for 1.8V and Beyond:, Semiconductor Research and Development Center, IBM Corporation, pp. 293-297.								
-	AN	Sakui, Koji et al., "A New Static Memory Cell Based on Reverse Base Current (RBC) Effect of Bipolar Transistor", ULSI Research Center, Toshiba Corporation, Japan, 44-IEDM 88 (4 pages								
	AO	Van der Wagt, J.P., et al., "RTD/HFET Low Standby Power SRAM Gain Cell", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998, pp. 6-9.								
	AP				Hight-Gain Lateral Bip on Devices, Vol. 38, N					248
EXAMINER					DATE CONSIDERED					

Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).